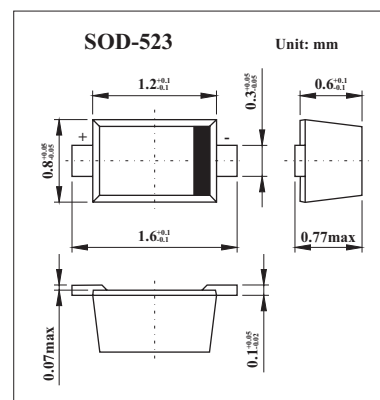


## Silicon Epitaxial Planar Pin Diode

## HVC134

## ■ Features

- Low capacitance. (C=0.4pF max)
- Low forward resistance. ( $r_f=2.0\ \Omega$  max)

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Value	Unit
Peak reverse voltage	$V_{RM}$	65	V
Reverse voltage	$V_R$	60	V
Forward current	$I_F$	100	mA
Power dissipation	$P_d$	150	mW
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current	$I_R$	$V_R = 60\text{ V}$			0.1	$\mu\text{ A}$
Reverse voltage	$V_F$	$I_F = 10\text{ mA}$			1.0	V
Capacitance	C	$V_R = 1\text{ V}, f = 1\text{ MHz}$			0.4	pF
Forward resistance	$r_f$	$I_F = 10\text{ mA}, f = 100\text{ MHz}$			2.0	$\Omega$
ESD-Capability *1		C = 100pF, R = 1.5K $\Omega$ , Both forward and reverse direction 5 pulse	200			V

Note

1. Failure criterion ;  $I_R > 0.1\ \mu\text{ A}$  at  $V_R = 60\text{ V}$ .

## ■ Marking

Marking	P4
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